

SEMITOP[®] 4

IGBT Module

SK100GD066T

Preliminary Data

Features

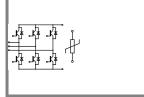
- One screw mounting module
 Fully compatible with SEMITOP[®]1,2,3
- Improved thermal performances by aluminium oxide substrate
- Trench IGBT technology
- CAL technology FWD
- Integrated NTC temperature sensor

Typical Applications*

- Inverter up to 22 kVA
- Typ. motor power 11 kW

Absolute Maximum Ratings T _s =			s = 25 °C, unless otherwise	• 25 °C, unless otherwise specified		
Symbol Conditions			Values	Units		
IGBT						
V _{CES}	T _j = 25 °C		600	V		
I _C	T _j = 175 °C	T _s = 25 °C	105	А		
		T _s = 70 °C	85	А		
I _{CRM}	I _{CRM} = 2 x I _{Cnom}		200	А		
V _{GES}			± 20	V		
t _{psc}	V_{CC} = 360 V; $V_{GE} \le 20$ V; VCES < 600 V	T _j = 125 °C	6	μs		
Inverse	Diode					
I _F	T _j = 175 °C	T _s = 25 °C	99	A		
		T _s = 70 °C	79	А		
I _{FRM}	I _{FRM} = 2 x I _{Fnom}		120	А		
Module						
I _{t(RMS)}				А		
T _{vj}			-40 +175	°C		
T _{stg}			-40 +125	°C		
V _{isol}	AC, 1 min.		2500	V		

Characteristics T _s =		25 °C, unless otherwise specified				
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
V _{GE(th)}	V_{GE} = V_{CE} , I_C = 1,6 mA		5	5,8	6,5	V
I _{CES}	V_{GE} = 0 V, V_{CE} = V_{CES}	T _j = 25 °C			0,005	mA
		T _j = 125 °C				mA
I _{GES}	V _{CE} = 0 V, V _{GE} = 20 V	T _j = 25 °C			600	nA
		T _j = 125 °C				nA
V _{CE0}		T _j = 25 °C		0,9	1,1	V
		T _j = 150 °C		0,8	1	V
r _{CE}	V _{GE} = 15 V	T _j = 25°C		5,5	7,5	mΩ
		T _j = 150°C		8,5	10,5	mΩ
V _{CE(sat)}	I _{Cnom} = 100 A, V _{GE} = 15 V	T _j = 25°C _{chiplev.}		1,45	1,85	V
		T _j = 150°C _{chiplev.}		1,65	2,05	V
C _{ies}				6,1		nF
C _{oes}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz		0,38		nF
C _{res}				0,18		nF
t _{d(on)}				144		ns
t, F	R_{Gon} = 32 Ω	$V_{\rm CC} = 300V$		128		ns
E _{on}	D 00 0	I _C = 100A		7		mJ
t _{d(off)}	$R_{Goff} = 32 \Omega$	$T_{j} = 150 \ ^{\circ}C$		1040		ns
t _f	di/dt = 2575 A/µs	V _{GE} = -7/+15 V		91		ns
E _{off}				6		mJ
R _{th(j-s)}	per IGBT			0,65		K/W



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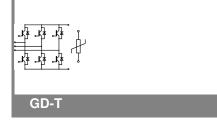
Typical Applications*

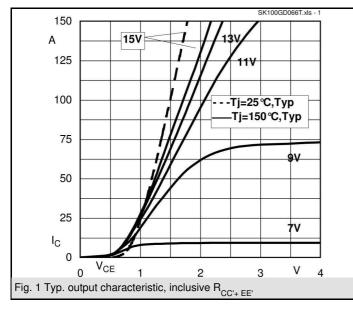
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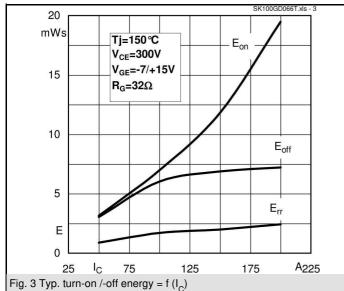
Symbol	Conditions		min.	typ.	max.	Units
Inverse D						
V _F = V _{EC}	I _{Fnom} = 100 A; V _{GE} = 0 V	T _j = 25 °C _{chiplev.}		1,3		V
		T _j = 150 °C _{chiplev.}		1,3		V
V _{F0}		T _j = 25 °C		0,95		V
		T _j = 150 °C		0,85		V
r _F		T _j = 25 °C		3,5		mΩ
		T _j = 150 °C		4,5		mΩ
I _{RRM}	I _F = 100 A	T _j = 150 °C		60		А
Q _{rr}	di/dt = 2575 A/µs	-		5,6		μC
E _{rr}	V _{CC} = 300V			1,7		mJ
R _{th(j-s)D}	per diode			0,8		K/W
M _s	to heat sink		2,5		2,75	Nm
w				60		g
Temperat	ture sensor					
R ₁₀₀	T _s = 100°C (R ₂₅ =5kΩ)			493±5%		Ω

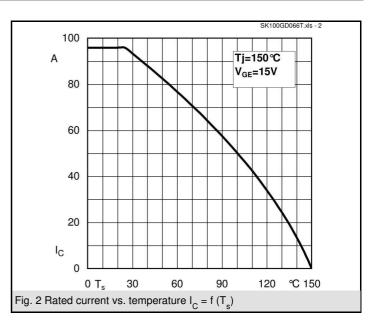
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

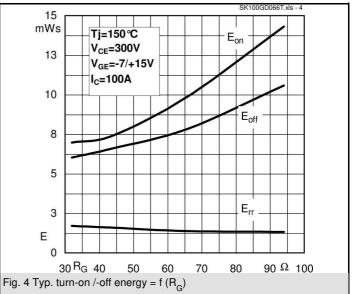
* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

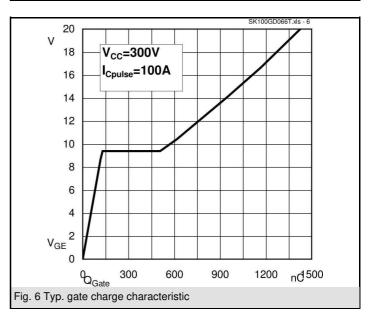


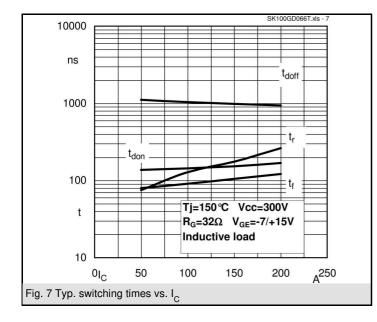


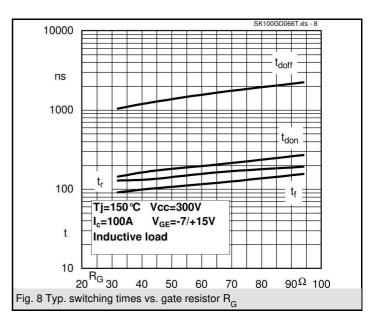


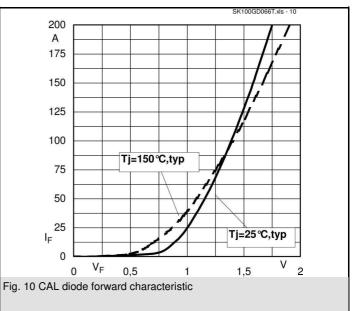












UL recognized



